

C. Material Growth & Characterization 분과

2020년 2월 14일(금), 09:00-10:30 / Room F (스페이스 I, 6층)

■ [FF1-C] Wide Bandgap Materials I (Ga₂O₃ & etc)

좌장: 박일규 교수 (서울과학기술대학교), 이형우 교수 (아주대학교)

FF1-C-1 09:00-09:30	<p>[초청]</p> <p>Development of Ultra Wide Bandgap Ga₂O₃ Materials for Next Generation Power Electronics Applications</p> <p>Youngboo Moon¹, Woosik Lee¹, Daejang Lee¹, and Jun-Seok Ha²</p> <p>¹UJL, ²School of Applied Chemical Engineering, Chonnam National University</p>
FF1-C-2 09:30-10:00	<p>[초청]</p> <p>Heteroepitaxial Growth of α-Ga₂O₃ Film on Sapphire Substrate by Hydride Vapor Phase Epitaxy</p> <p>Dae-Woo Jeon</p> <p>KICET</p>
FF1-C-3 10:00-10:15	<p>Hetero Epitaxial Thin Film Growth on a New Substrate of High Quality BaZrO₃ Single Crystal</p> <p>Daehwan Park¹, Nguyen Xuan Duong², Gye-Hyeon Kim³, Ki-Bog Park^{1,3}, Changhee Sohn^{1,3}, Tae Heon Kim², and Yoon Seok Oh^{1,3}</p> <p>¹Department of Physics, UNIST, ²Department of Physics and Energy Harvest Storage Research Center (EHSRC), University of Ulsan, ³School of Natural Science, UNIST</p>
FF1-C-4 10:15-10:30	<p>Tuning of Metal-to-Insulator Transition in Epitaxial Bilayer Nickelate Thin Films through Sub-layer Thickness Control</p> <p>Jongmin Lee¹, Seyeop Jeong⁶, Byeong-Gwan Cho², Tae Kwon Lee³, Jiwoong Kim⁴, Sangmo Kim⁵, Chung Wung Bark⁵, Sungkyun Park⁴, Jong Hoon Jung³, Tae Young Koo², Sanghoon Kim⁶, Tae Heon Kim⁶, and Sanghan Lee¹</p> <p>¹School of Materials Science and Engineering, GIST, ²Pohang Accelerator Laboratory, ³Department of Physics, Inha University, ⁴Department of Physics, Pusan National University, ⁵Department of Electrical Engineering, Gachon University, ⁶Department of Physics, University of Ulsan</p>